GATE XE 2007

1

(GATE 2007 XE)

(GATE 2007 XE)

d) 3

AI25BTECH11003 - Bhavesh Gaikwad

SECTION A: ENGINEERING MATHEMATICS (COMPULSORY)

1. Let $M = \begin{pmatrix} 1 & 1 & 1 \\ 0 & 1 & 1 \\ 0 & 0 & 1 \end{pmatrix}$. Then the maximum number of linearly independent eigenvectors

c) 2

a) 0

b) 1

2. Let $\lim_{x\to\frac{\pi}{2}}\frac{\sin^2(2x)}{\left(x-\frac{\pi}{2}\right)^2}$. Then L is equal to :

	a) -4	b) 0	c) 2	d) 4
3.	Let $f(z) = \frac{1}{1-z^2}$. The z=1 is:	coefficient of $f(z) = \frac{1}{z}$	$\frac{1}{-1}$ in the Laurent expansion	ansion of f(z) about (GATE 2007 XE)
	a) -1	b) $-\frac{1}{2}$	c) $\frac{1}{2}$	d) 1
4.	Let $u(x,t)$ be the solu $x < \infty$ $u(x,0) = x + 5$	ation of the initial value, $\frac{\partial u}{\partial t} (x,0) = 0$. Then		$\frac{\partial^2 u}{\partial x^2}$,; $t > 0$,; $-\infty <$ (GATE 2007 XE)
	a) 7	b) 13		d) 26
5.	correct answers to tw	nswer at least three questions and guest	TRUE/FALSE question uestions correctly. Bot is the answers to the reference test is equal to:	h of them know the emaining three. The
	a) $\frac{6}{32}$	b) $\frac{7}{32}$	c) $\frac{1}{4}$	d) $\frac{3}{4}$
6.	The equation $g(x) =$ an initial approximat at the $(n+1)$ th iteration	ion x_n near the simple	n-Raphson iteration me root a. If x_{n+1} is the	
				(GATE 2007 XE)

(GATE 2007 XE)

d) n solutions

c) $x_{n+1} = g(x_n)$ d) $x_{n+1} = \frac{x_n, g'(x_n) - g(x_n) + 2x_n}{g'(x_n) + 1}$

c) exactly one so-

lution

0.		n eigenvector of P co	rresponding to a nonz	
	a) Rx is an eigenv sponding to eigenb) Rx is an eigenv sponding to eigen	vector of Q corre-	 c) R⁻¹x is an eigen sponding to eige d) R⁻¹x is an eigen sponding to eige 	nvalue λ of Q expression of Q corresponds to Q
9.	Let M be a 2×2 ma	trix with eigenvalues	1 and 2. Then M^{-1} is	s: (GATE 2007 XE)
	a) $M-3I$	b) 3 <i>I</i> – <i>M</i>	c) 2 <i>I</i> – <i>M</i>	d) $M^{-1} - 3I$
10.	The number of $n \times n$ r is:	matrices that are simul	taneously Hermitian,	unitary and diagonal (GATE 2007 XE)
	a) 2^n	b) n^2	c) 2n	d) 2
11.	Let $M = \begin{pmatrix} 1 & b & a \\ 0 & 2 & c \\ 0 & 0 & 1 \end{pmatrix}$ (GATE 2007 XE)	, where a, b, c are r	real numbers. Then M	I is diagonalizable:
	a) for all values of a, b, c	b) only when $bc \neq a$	c) only when $b + c = a$	d) only when bc = a
12.	The maximum value is:	of the function $2x + 3$	sy + 4z on the ellipsoid	$d 2x^2 + 3y^2 + 4z^2 = 1$
				(GATE 2007 XE)
	a) 2	b) 3	c) 6	d) 9
13.	Let $f : \mathbb{R} \to \mathbb{R}$ be a t $n = 1, 2, 3, \dots$ Then:		al valued function suc	th that $f\left(\frac{1}{n}\right) = 1$ for (GATE 2007 XE)

7. Let Ax = b be a system of m linear equations in n unknowns with m; n and $b \neq 0$.

8. Let R be an $n \times n$ nonsingular matrix. Let P and Q be two $n \times n$ matrices such that

infinitely many

solutions

a) $x_{n+1} = \frac{x_n g'(x_n) - g(x_n)}{1 - g'(x_n)}$ b) $x_{n+1} = \frac{x_n g'(x_n) - g(x_n)}{g'(x_n) - 1}$

Then the system has:

a) n - m solutions

b) either zero or

d) $\frac{\pi}{2}$

d) $2\pi i$

(GATE 2007 XE)

16.	Let $f(x+iy) = u(x, y)$ satisfying $2u^2 + 3v^2 =$		tic function defined o	n the complex plane (GATE 2007 XE)
	a) f is a constantb) f(z) = kz for	some nonzero real k	c) $u(x, y)$ = $\frac{\cos(x+y)}{\sqrt{2}}$	d) $v(x, y)$ = $\frac{\sin(x-y)}{\sqrt{3}}$
17.	The value of $\oint_C (xy^2)$ anticlockwise direction		dy along the circle C	$x^2 + y^2 = 4$ in the (GATE 2007 XE)
	a) -16π	b) -4 <i>π</i>	c) 4π	d) 16π
18.	The volume of the prox-axis and the lines your is: a) 2 b) 4 c) 6 d) 10		e triangle in the xy-pl whose top lies in the	_
19.	The general solution	of $x \frac{\partial z}{\partial x} (z^2 - y^2) + (x - y^2)$	$-2)\frac{\partial z}{\partial y} = (-x)\frac{\partial z}{\partial z}$ is:	(GATE 2007 XE)
	a) $F(x^2 + y^2 + z^2, xyz) = 0$	b) $F(x^2 + y^2 - z^2, xyz) = 0$	c) $F(x^2 - y^2 + z^2, xyz) = 0$	d) $F(-x^2 + y^2 + z^2, xyz) = 0$
20.	Choose a point unifor X denote the distance X is:	=	e disc $x^2 + y^2 \le 1$. Let ne center of the disc.	
	a) 1/16	b) 1/17	c) $\frac{1}{18}$	d) $\frac{1}{19}$

a) f'(0) = 0 b) f'(0) = 1 c) 0 < f'(0) < 1 d) f'(0) > 1

14. Let $f(x) = \int_0^{\sqrt{x}} \sin t \, dt$ for $x \ge 0$. Then $f'\left(\frac{x}{2}\right)$ is equal to: (GATE 2007 XE)

c) 1

c) 0

b) π

15. The value of the contour integral $\oint_{|z|=1} \frac{4z^2+1}{\cosh z} dz$ is equal to:

b) $\pi \cosh(i/2)$

a) 0

a) $2\pi i \cosh(i/2)$

22.	If a polynomial of de (3,99), (4,187), then	-	a function f(x) at the	points (0,3), (1,13), (GATE 2007 XE)
	a) 20	b) 36	c) 43	d) 58
23.	Let $f(x) = x^2$ for $-\pi$ is:	$\leq x \leq \pi$ and $f(x+2\pi)$	= f(x). The Fourier so	eries of f in $[-\pi, \pi]$ (GATE 2007 XE)
	a) $\frac{\pi^2}{3} + 4 \sum_{n=1}^{\infty} \frac{\cos nx}{n^2}$ b) $\frac{\pi^2}{3} + 4(-1)^n \sum_{n=1}^{\infty}$	$\frac{\cos nx}{n^2}$	c) $\frac{\pi^2}{3} + 4(-1)^n \sum_{n=1}^{\infty} 1$ d) $\frac{\pi^2}{3} + \sum_{n=1}^{\infty} \frac{\cos nx}{n^2}$	$\frac{\cos nx}{n^2}$
24.	The sum of the absol	ute values of the Four	rier coefficients of f is	: (GATE 2007 XE)
	a) $\frac{\pi^2}{6}$	b) $\frac{\pi^2}{3}$	c) $\frac{2\pi^2}{3}$	d) π^2
25.	Let $y(x) = \sum_{n=0}^{\infty} a_n x^n$ (GATE 2007 XE)	be a solution of $\frac{d^2y}{dx^2}$ +	xy = 0. The value of	a_n is:
	a) 0	b) 1	c) 2	d) 3
26.	The solution of the a (GATE 2007 XE)	bove differential equa	tion satisfying $y(0) =$	1 and $y'(0) = 0$ is:
	a) $y(x) = 1 + \frac{x^2}{2! \cdot 3} - \frac{1}{2}$ b) $y(x) = 1 - \frac{2 \cdot 3x^2}{1} + \frac{1}{2}$	$\frac{x^4}{2\cdot 3\cdot 5\cdot 6} + \dots$	c) $y(x) = 1 +$ d) $y(x) = 1$	
27.	The potential $u(x,y)$ s = 0 , $x = \pi$, $y = 0$ a	satisfies $\frac{\partial^2 u}{\partial x^2} + \frac{\partial^2 u}{\partial y^2} = 0$ in an annual nonzero at $y = \pi$.	in $0 \le x \le \pi$, $0 \le y \le$ The potential is:	π , with $u = 0$ on x (GATE 2007 XE)
	a) $u = \sum A_n \cosh(nx)$ b) $u = \sum A_n \sin(nx)$		c) $u = \sum A_n \sinh(nx)$ d) $u = \sum A_n \sin(nx)$ s	
28.	If $y = \pi$ edge is at po	otential $sin(x)$, then:		(GATE 2007 XE)
	a) $u = \frac{\sin(nx) \sinh(ny)}{\sinh(n\pi)}$ b) $u = \frac{\sin x \sinh y}{\sinh \pi}$		c) $u = \frac{\sin x \cosh y}{\cosh \pi}$ d) $u = \frac{\cosh(nx)\sin(ny)}{\cosh(n\pi)}$	

—END OF SECTION—

21. If Runge–Kutta method of order 4 is used to solve the differential equation $\frac{dy}{dx} = f(x)$, y(0) = 0, in the interval [0,h] with step size h, then (GATE 2007 XE)

a) $y(h) = \frac{h}{6}[f(0) + 4f(h/2) + f(h)]$

b) $y(h) = \frac{h}{6}[f(0) + f(h)]$

c) y(h) = h[f(0) + f(h)]d) $y(h) = \frac{h}{6}[f(0) + 2f(h/2) + f(h)]$

d) 112

SECTION B: COMPUTATIONAL SCIENCE

1) If the 7-base representation of a number is 123, then its octal representation is

c) 111

b) 103

2) Consider the following four FORTRAN statements:

(GATE 2007 XE)

a) 102

S1: X = 5**3

S2: X = (-5)**3.0 S3: X = 5**-3 S4: X = 5**3.0 Which of the follo (GATE 2007 XE)	owing sets contains the	valid statements fron	n above?
a) {S1, S3}	b) {S1, S4}	c) {S2, S3}	d) {S2, S4}
3) Which of the followard (GATE 2007 XE)	owing sets contains the	set of the basic data	types in C?
a) {char, int, floab) {char, boolean		c) {char, int, long, d) {char, int, float,	, short, float, double} , void}
4) If a root of $f(x)$ = with $x_0 = 0.5$, the (GATE 2007 XE)	$= x^2 - 2x + 1 = 0 \text{ is ob}$ convergence rate is	otained by using itera	tion $x_{n+1} = x_n - \frac{f(x_n)}{f'(x_n)}$
a) 1	b) 1.62	c) 1.84	d) 2
	of the eigenvalues of a S_1 natrix Q. If $S_1 = S_2$, th		he sum of eigenvalues (GATE 2007 XE)
a) $\begin{pmatrix} 4 & 1 \\ 3 & 5 \end{pmatrix}$ and $\begin{pmatrix} 3 \\ 3 \end{pmatrix}$ b) $\begin{pmatrix} 3 & 4 \\ 5 & 1 \end{pmatrix}$ and $\begin{pmatrix} 3 \\ 5 \end{pmatrix}$	2 5) 4 1)	c) $\begin{pmatrix} 4 & 1 \\ 3 & 5 \end{pmatrix}$ and $\begin{pmatrix} 3 \\ 5 \end{pmatrix}$ d) $\begin{pmatrix} 4 & 3 \\ 5 & 5 \end{pmatrix}$ and $\begin{pmatrix} 4 \\ 5 \end{pmatrix}$	1 1) 3 5)
	value of $y(x)$ at $x = x_i$ at $x = x_i$ is approxima		
a) $\frac{y_{i+1}-2y_i+y_{i-1}}{h^2}$	b) $\frac{y_{i+1} - y_i + y_{i-1}}{h^2}$	c) $\frac{y_{i+1}-2y_i+y_{i-1}}{2h}$	d) $\frac{y_{i+1} - y_i + y_{i-1}}{2h^2}$
7) The minimum nur correct up to 3 de	mber of terms required cimal places is:	in e^x series expansion	n to evaluate at $x = 1$ (GATE 2007 XE)

d) 5

d) 0.80

(GATE 2007 XE)

	a) symmetric	b) non-symmetric	c) singular	d) non-singular
10)	If two eigenvalues of (GATE 2007 XE)	the matrix $M = \begin{pmatrix} 2 \\ 1 \\ 0 \end{pmatrix}$	$\begin{pmatrix} 6 & 0 \\ p & 0 \\ 0 & 3 \end{pmatrix}$ are -1 and 4, the	nen p is:
	a) 4	b) 2	c) 1	d) -1
11)	Consider the system: x + 10y = 5 y + 5z = 1 10x - y + z = 0 On applying Gauss–S (GATE 2007 XE)	Seidel method, x corre	ect up to 4 decimal pla	aces is:
	a) 0.0385	b) 0.0395	c) 0.0405	d) 0.0410
12)	The graph $y = f(x)$ pathe x-value where $y = f(x)$		1,-1), (2,3). Using Lag	range interpolation, (GATE 2007 XE)
	a) 1.375	b) 1.475	c) 1.575	d) 1.675
13)	The equation of the b	est fit line (least squa	nres) for: x: 1 2 3 4 5.	y: 14 13 9 5 2 is: (GATE 2007 XE)
	a) $y = 18 - 3x$	b) $y = 18.1 - 3.1x$	c) $y = 18.2 - 3.2x$	d) $y = 18.3 - 3.3x$
14)	Solve $\frac{dy}{dx} = xy^2$, y(1) XE)	= 1 by Euler's metho	od, step $h = 0.1$, find y	(1.2): (GATE 2007
	a) 1.1000	b) 1.1232	c) 1.2210	d) 1.2331
15)	The local error of sc Taylor series is:	heme: $y_{n+1} = y_n + \frac{h}{12}$	$(5y_{n+1} + 8y_n - y_{n-1}) b$	y comparison with (GATE 2007 XE)

b) 7

b) 0.68

a) 8

a) 0.65

will always be:

c) 6

c) 0.73

8) The iteration $x_{n+1} = \frac{1}{1+x_n^2}$ converges to a real number x in the interval (0,1) with $x_0 = 0.5$. The value of x correct up to 2 decimal places is: (GATE 2007 XE)

9) If the diagonal elements of a lower triangular square matrix A are all \neq 0, then A

				7	
	a) O(h)	b) $O(h^2)$	c) $O(h^3)$	d) $O(h^4)$	
16)	The area between $y =$ with $h = 0.5$ is:	$1 - x^2$ and x-axis from	m x = -1 to x = 1 using	ng Trapezoidal rule	
	with ii = 0.3 is.			(GATE 2007 XE)	
	a) 1.20	b) 1.23	c) 1.25	d) 1.33	
17)	Iteration: $x_{n+1} = \sqrt{a}$	$\left(1 + \frac{1}{3a^2}\right), \ a > 0 \text{ conve}$	erges to:	(GATE 2007 XE)	
	a) \sqrt{a}	b) a	c) $\sqrt[3]{a}$	d) a^2	
18)	If $m = 01001101_2$, n (GATE 2007 XE)	$= 00101011_2$, then m	n-n in binary is:		
	a) 00010010	b) 00100010	c) 00111101	d) 00100001	
19)	P: Local variable is used only within its block and sub-blocks. Q: Global variables are declared outside all blocks. R: Extern variables are used for sharing between compilation units. S: Default all global variables are extern.: (GATE 2007 XE)				
	a) P, Q	b) P, Q, R	c) P, Q, S	d) P, Q, R, S	
20)	Recursive function:				

```
integer function g(m,n)
if (n == 0) then
r = m
else if (m = 0) then
r = n + 1
else if ((n - n/2*2) == 1) then
r = g(m-1, n+1)
else
r = g(m-2, n/2)
end if
```

If called with (6,6), returns:

```
a) 2
```

b) 4

c) 6

d) 8

21) Function:

```
real function print_value(x) i = 0; sum = 2.0; term = 1.0 do while (term > 0.00001) term = x * term / (i+1) sum = sum + term i = i + 1 end do Called with x = 1 outputs close to:
```

(GATE 2007 XE)

- a) ln2
- b) ln3
- c) 1 + e
- d) e

22) C-program:

```
char s[80], *p;
int sum = 0;
p = s;
gets(s);
while (*p)
if (*p == '1') sum = 2*sum + 1;
else if (*p == '0') sum = sum * 2;
else printf("invalid string");
p++;
printf("%d", sum);
```

Input 10110 outputs:

(GATE 2007 XE)

a) 31

b) 28

c) 25

d) 22

23) Given:

```
int m[3] = 1,3,5, 7,9,11, 13,15,17;
sum=0;
for (i=0; i<3; i++)
for (j=2; j>1; j-)
sum += m[i][j]*m[i][j-1];
prints sum = ?:
```

- a) 369
- b) 361
- c) 303
- d) 261

24) Values printed after calling:

```
void print mat(int mat[][3]) {
int (*p) = &mat[1];
printf("%d and %d", (*p)[1], (*p)); }:
```

(GATE 2007 XE)

a) 3 and 5

b) 7 and 9

c) 9 and 11

d) 13 and 15

25) Quadrature formula: $\int_0^1 f(x) dx \approx \frac{1}{8} \left[f(0) + 2bf(0.25) + 2f(0.5) + 2df(0.75) + f(1) \right]$. If used as Simpson's $\frac{1}{3}$ rule: (GATE 2007 XE)

a) b = d = 1 b) b = d = 2 c) b = 2d = 1 d) b = 2d = 2

26) Using b, d from Q25, $\int_0^1 \frac{dx}{1+x}$ correct to 4 decimal places is:

(GATE 2007 XE)

a) 0.3091

b) 0.3121

c) 0.3151

d) 0.3191

27) Solve $\frac{dy}{dx} = f(x, y) = 2xy$, y(0) = 1, y(0.2) = 1.0408, y(0.4) = 1.1735, y(0.6) = 1.04081.4333. Predictor scheme: (GATE 2007 XE)

a)
$$y_{n+1} = y_n + \frac{4h}{3}(2f_{n-1} - f_{n-2} + 2f_{n-3})$$

a)
$$y_{n+1} = y_n + \frac{4h}{3}(2f_{n-1} - f_{n-2} + 2f_{n-3})$$
 c) $y_{n+1} = y_{n-1} + \frac{h}{3}(4f_n - 5f_{n-1} + 4f_{n+1})$

b)
$$y_{n+1} = y_{n-3} + 3\frac{h}{4}(2f_{n-2} - f_{n-1} + 2f_n)$$

b)
$$y_{n+1} = y_{n-3} + 3\frac{h}{4}(2f_{n-2} - f_{n-1} + 2f_n)$$
 d) $y_{n+1} = y_{n-3} + \frac{h}{4}(2f_{n-1} - f_{n-2} + 2f_{n-3})$

28) Using correct predictor from Q27, y(0.8) =:

(GATE 2007 XE)

a) 1.8680

b) 1.8750

c) 1.8890

d) 1.9055

—END OF SECTION—

SECTION C: ELECTRICAL SCIENCES

1. Assuming all components are ideal, the average power delivered by the DC voltage source in the network is:

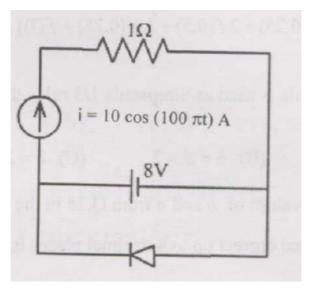


Fig. 1..1: Circuit

(GATE 2007 XE)

a) -28W

b) 0W

c) 64W

d) 80W

2. An ideal transformer with 10 turns in primary and 30 turns in secondary has its primary connected to external circuits as shown. The current provided from the sinusoidal voltage source is:

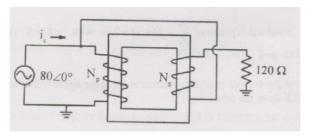


Fig. 2..1: Transformer

(GATE 2007 XE)

- a) $0.67 \angle 0^{\circ}$
- b) 2.0∠0°
- c) 2.67∠0°
- d) 10.67∠0°
- 3. In a three-phase, Y-connected squirrel cage induction motor, if N_s is synchronous speed, N_r is rotor speed and s is slip, then speeds of airgap field and rotor field w.r.t. (GATE 2007 XE) stator structure will be respectively:
 - a) N_s , N_s
- b) N_r , N_s c) N_r , N_r
- d) N_s , N_r
- 4. The equivalent conductance of a forward biased diode at room temperature is: (GATE 2007 XE)
 - a) constant

c) proportional to V^2

b) proportional to V

- d) proportional to $\exp(KV)$
- 5. An 8-bit signed magnitude number (10101010)₂ represents the decimal: (GATE 2007 XE)
 - a) -42
- b) -85
- c) -86
- d) -176
- 6. A 10-bit DAC with full-scale 5 V has resolution and step size respectively: (GATE 2007 XE)
 - a) 0.0978%, 500 mV

c) 0.195%, 9.76 mV

b) 0.0978%, 4.88 mV

d) 0.195%, 500 mV

7. A power source has open circuit voltage 24 V and short circuit current 16 A. Terminal characteristics shown below: (GATE 2007 XE)

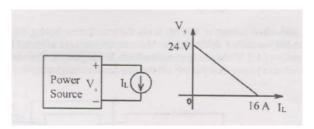


Fig. 7..1: Circuit

- a) Load current = 16 A
- b) Source voltage = 24 V

- c) Load power = 96 W
- d) Load power = 384 W
- 8. A 100 kVA, 11 kV/415 V transformer with 2% winding resistance and 4% leakage reactance. Voltage regulation at rated KVA, 0.8 pf lagging load is: (GATE 2007 XE)
 - a) 2%
- b) 4%
- c) 4.8%
- d) 6%
- 9. Source voltage of three-phase network is 11 kV. Line voltage at load end and phase angle w.r.t source voltage:

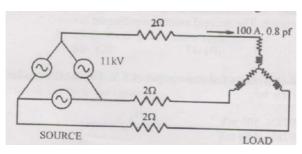


Fig. 9..1: Network

- a) $10.7 \text{ kV}, 0^{\circ}$
- b) 10.7 kV, 1.08° lagging

- c) 10.7 kV, 1.08° leading
- d) 11 kV, 1.08° lagging

10. A sine-wave voltage at 400 Hz feeds a transformer with 50 primary turns, core saturation flux density 1.2 T, core area 10 cm², relative permeability 1000. Max amplitude without saturation is: (GATE 2007 XE)

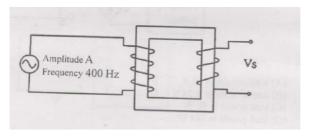


Fig. 10..1: Transformer

- a) 24 V
- b) 48 V
- c) 75.4 V d) 150.8 V
- 11. A 415 V/240 V, 1 kVA, 50 Hz transformer has leakage reactance 4%. Leakage inductance of secondary winding is: (GATE XE 2007)
 - a) 7.3 mH
- b) 21.9 mH c) 183 mH
- d) 2300 mH
- 12. Transformer with 100 turns primary and 50 turns secondary on C core with 1.0 mm airgap, core area 1.0 cm², primary connected to $v_p = 10\cos(2000\pi t)$ V. Peak MMF of primary winding is: (GATE 2007 XE)

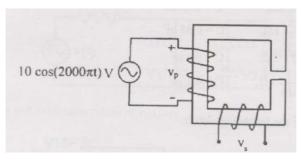


Fig. 12..1: Transformer

- a) 126.65 AT
- b) 253.3 AT
- c) 314 AT d) 1000 AT

13. PMDC generator armature resistance 0.5 Ω , speed 600 rpm, voltage 60 V. When armature connected to 150 V DC source, starting current and line current at 1200 rpm are:

(GATE 2007 XE)

- a) 120 A, 60 A
- b) 300 A, 60 A
- c) 120 A, 120 A
- d) 300 A, 120 A
- 14. 4-pole DC machine with lap wound armature radius 14.2 cm, length 26.3 cm, poles cover 80% armature, 39 coils 5 turns each, flux per pole is: (GATE 2007 XE)
 - a) 15.95 mWb
- b) 31.9 mWb
- c) 39.9 mWb
- d) 63.8 mWb
- 15. DC shunt motor at 1400 rpm fed by 220 V DC, line current 101 A, field resistance 220 Ω , armature resistance 0.2 Ω . Mechanical power developed

(GATE 2007 XE)

- a) 22.22 kW
- b) 22 kW
- c) 20 kW
- d) 2 kW
- 16. A transistor oscillator uses a 3-section RC phase shift circuit. Oscillation frequency 10 k rad/s, suitable R and C values are: (GATE 2007 XE)
 - a) $R = 3 k\Omega$, $C = 0.33 \mu F$

c) $R = \frac{1}{\sqrt{3}} k\Omega$, $C = 0.1 \,\mu F$

b) $R = 1 k\Omega$, $C = 0.33 \mu F$

- d) $R = 1 k\Omega / \sqrt{3}$, $C = 0.1 \mu F$
- 17. For transistor circuit given, $\beta = 50$, $C \rightarrow \infty$. The quiescent collector current I_{CQ} is: (GATE 2007 XE)

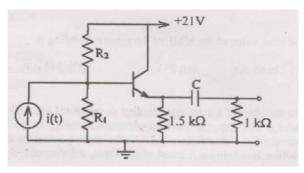


Fig. 17..1: Transistor Circuit

- a) 7 mA
- b) 10 mA
- c) 14 mA
- d) 35 mA

18. The CMOS circuit shown below represents:

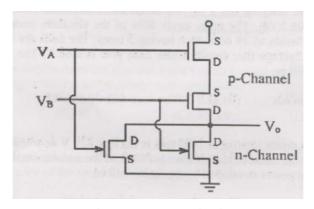


Fig. 18..1: CMOS circuit

- a) AND gate
- b) NAND gate
- c) OR gate
- d) NOR gate
- 19. In the circuit below, $v(t) = 3\cos\omega t$, diode cut-in voltage 0.7 V, $V_1 = 2V$, $V_2 = 1V$. Max and min values of $v_o(t)$ are: (GATE 2007 XE)

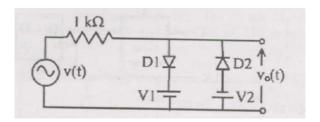


Fig. 19..1: Circuit

- a) +2.3 V, -1.7 V b) +2.7 V, -1.7 V c) +1.3 V, -0.3 V d) +2.3 V, -1.3 V

20. Given $v(t) = 2\cos 2000\pi t$ and ideal op-amp as shown, current $i_x(t)$ in 5 k Ω resistor

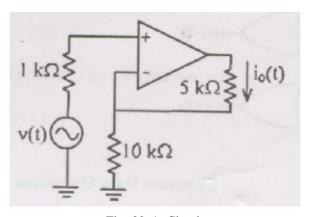


Fig. 20..1: Circuit

(GATE 2007 XE)

a) $0.66 \text{ mA } \cos 2000\pi t$

c) $0.2 \text{ mA } \cos 2000\pi t$

b) $0.33 \text{ mA } \cos 2000\pi t$

- d) $0.1 \text{ mA } \cos 2000\pi t$
- 21. Simplified logic expression of circuit shown is:

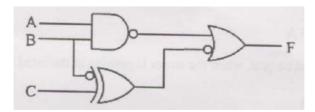


Fig. 21..1: Logic Gate

a)
$$AB + BC$$

b)
$$AB + C$$
 c) $A + B + C$

d)
$$\overline{A+B+C}$$

22. A D flip-flop is converted to T flip-flop by a logic circuit shown. The logic circuit is:

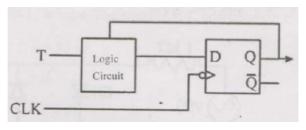
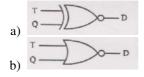
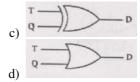


Fig. 22..1: Logic Circuit

(GATE 2007 XE)





23. Three-phase, 4-pole, 400 V, 50 Hz, Y-connected induction motor with parameters $R_2=0.35\Omega$, $X_2=0.25\Omega$, $X_m=25\Omega$. Stator impedance and iron loss neglected. Starting current for direct-on-line start is:

(GATE 2007 XE)

- a) 542.36 A
- b) 659.83 A
- c) 939.4 A
- d) 1142.85 A

24. Full load current at rated speed is:

- a) 13.88 A
- b) 24.04 A
- c) 33.99 A
- d) 41.64 A

25. The switch S_1 turns on/off repeatedly at 20 kHz, with ON duration 20 μ s. Switch & diode ideal. The average load voltage V_o is: (GATE 2007 XE)

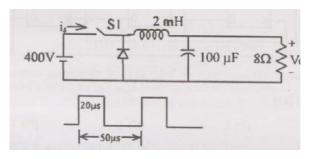


Fig. 25..1: Circuit

- a) 667 V
- b) 400 V
- c) 240 V
- d) 160 V
- 26. Average source current I_s provided by 400 V source is:

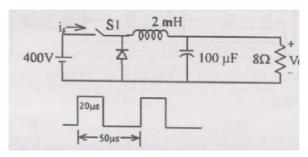


Fig. 26..1: Circuit

- a) 8 A
- b) 12 A
- c) 20 A
- d) 160 A

27. Divide by N counter using J-K flip-flops shown below. The value of N is:

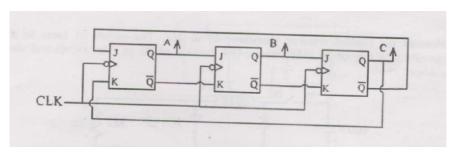


Fig. 27..1: Circuit

(GATE 2007 XE)

a) 4

b) 5

c) 6

d) 7

28. Counter output (Q27) goes to 3-to-8 decoder, LEDs as shown. LEDs that never glow are:

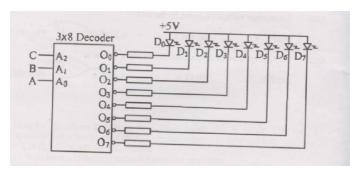


Fig. 28..1: LED Circuit

(GATE 2007 XE)

- a) D_0 and D_7 b) D_0 and D_2 c) D_2 and D_5 d) D_5 and D_7

-END OF SECTION-

SECTION D: FLUID MECHANICS

1. A projection manometer measures the dynamic pressure of an airstream ($\rho = 1.2 \text{ kg/m}^3$). The manometric liquid is alcohol (specific gravity 0.8), least count 0.1 mm, $g = 10 \text{ m/s}^2$, water density $\rho = 1000 \text{ kg/m}^3$. The lowest measurable velocity is:

	a)	$\sqrt{3}/2$ m/s	b) $2/\sqrt{3}$ m/s	c)	$\sqrt{3}$ m/s	d) 2 m/s
2.	The	velocity of soun	d:			(GATE 2007 XE)
		is a thermodynar is constant for a			depends on the vo	elocity field ar or turbulent flow
3.	The	e mass balance eq	uation			
	$\frac{\partial \rho}{\partial t} + \frac{\partial (\rho u)}{\partial x} + \frac{\partial (\rho v)}{\partial y} = 0$					
	holo	ds for:				(GATE 2007 XE)
		compressible	compressible/in-		• • • • • • • • • • • • • • • • • • • •	ncompressible only ble or incompress-
4.		e non-dimensional cosity μ is:	l number from speci	fic	heat c, thermal c	onductivity k, and (GATE 2007 XE)
	a)	$\frac{kc_p}{\mu}$	b) $\sqrt{\frac{ku}{c_p}}$	c)	$\frac{k\mu}{c_p}$	d) $\frac{\mu c}{k}$
5.	5. In a turbulent boundary layer, wall shear stress is $\tau_w = \mu \left. \frac{du}{dy} \right _{\text{wall}}$, where u is velocity parallel to the wall, y is perpendicular. Here, μ denotes (GATE 2007 XE)					
	b)	molecular viscos turbulent eddy vi effective viscos	scosity	d)	molecular effective viscosity lar	less than molecu-

6. Flow separation may occur if the flow is:

(GATE 2007 XE)

- a) viscous, positive streamwise pressure gradient
- b) viscous, negative streamwise pressure gradient
- c) inviscid, positive streamwise pressure gradient
- d) inviscid, negative streamwise pressure gradient
- 7. A solid sphere and hollow cube have the same surface area. The buoyancy force ratio (sphere:cube), fully submerged, is: (GATE 2007 XE)
 - a) $\frac{\pi^2}{4}$

- b) $\frac{\pi}{6}$
- c) $\frac{\pi}{9}$

- d) $\frac{\pi}{67}$
- 8. For steady 2D incompressible flow, if temperature T(x, y) is constant along a streamline, the streamline equation is: (GATE 2007 XE)
- a) $\frac{\partial T}{\partial x} = \frac{\partial T}{\partial y} \cdot \frac{dy}{dx}$ b) $\frac{\partial T}{\partial x} \cdot \frac{dy}{dx} = \frac{\partial T}{\partial y}$ c) $\frac{\partial T}{\partial y} \cdot \frac{dy}{dx} = \frac{\partial T}{\partial x}$ d) $\frac{\partial T}{\partial y} = \frac{\partial T}{\partial x} \cdot \frac{dy}{dx}$
- 9. In a 2D laminar boundary layer with constant free-stream velocity, the signs of material acceleration (parallel, perpendicular to wall) near the wall are:

- a) +, -
- b) -, +
- c) +, +
- d) -, -
- 10. Water enters a pipe (area A) and branches into sections (areas A_2 , A_3). Velocities at one instant: $V_1 = 2 \text{ m/s}$, $V_2 = 3 \text{ m/s}$, $V_3 = 5 \text{ m/s}$. At another, $V_1 = 3 \text{ m/s}$, $V_2 = 4 \text{ m/s}$. Find V_3 : (GATE 2007 XE)

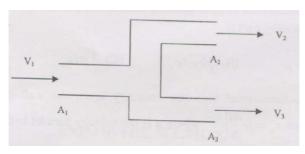


Fig. 10..1: Pipe Diagram

- a) 5 m/s
- b) $6 \,\mathrm{m/s}$
- c) 7 m/s
- d) 8 m/s

- 11. In 2D incompressible irrotational flow, u = 2x + 3y. The y-component of velocity is: (GATE 2007 XE)
 - a) 2y 3x
 - b) 2y + 3x
 - c) -2y + 3x
 - d) -2y 3x
- 12. For steady 2D flow with u = 6y, v = 0 (y is vertical distance), the angular velocity and shear strain rate are: (GATE 2007 XE)
 - a) -3, 3
- b) 3, -3 c) 3, -6
- d) -6, 3
- 13. In steady 2D incompressible flow, the stream function ψ obeys: $\frac{\partial^2 \psi}{\partial x^2} + \frac{\partial^2 \psi}{\partial x^2} = 4$. A solution is: (GATE 2007 XE)
 - a) $\psi = x^2 + y^2$ b) $\psi = y^2 x^2$ c) $\psi = xy$
- d) $\psi = x + y$
- 14. A uniform stream of ideal fluid (velocity *U*, pressure *p*) flows past a circular cylinder. Wall velocity is $V = 2U \sin \theta$. Pressure coefficient $C_p = \frac{P - P_{\infty}}{0.50U^2}$. The minimum C_p on the cylinder is:

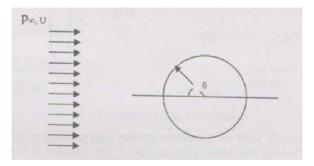


Fig. 14..1: Circular Cylinder

(GATE 2007 XE)

a) 1

- b) -1
- c) -3
- d) -4

(GATE 2007 XE)

a) 4×10^{-6}	b) 8×10^{-6}	c) 4×10^{-7}	d) 8×10^{-7}			
16. Water flows through Darcy friction factor mate pressure drop XE)	or: $f = 64/\text{Re}$ (lami	e at π kg/s, $\mu = 0.001$ N nar), $f = 0.316$ Re ^{-0.25}	$(s/m^2, \rho = 1000 \text{ kg/m}^3)$. (turbulent). Approxi- (GATE 2007)			
a) 20 Pa/m	b) 120 Pa/m	c) 480 Pa/m	d) 960 Pa/m			
17. Constant pressure $\mu = 1.79 \times 10^{-5} \text{ Ns/s}$	boundary layer over (m^2) . Transition at x_{cr}	a 3 m plate, $U = 60$ = 0.1 m. If $U = 120$ r	0 m/s, $\rho = 1.23 \text{ kg/m}^3$, n/s, new x_{cr} is: (GATE 2007 XE)			
a) 0.2 m	b) 0.1 m	c) 0.05 m	d) 0.005 m			
18. For a laminar bound of $\partial u/\partial y$ with y is:	dary layer with const	ant free-stream velocit	y ($\frac{dp}{dx}$ =0), the variation (GATE 2007 XE)			
a) $\frac{y}{\partial u/\partial y}$		c) $\frac{y}{\partial u/\partial y}$				
b)		$d) \qquad \frac{\sqrt{\partial u/\partial y}}{\partial u/\partial y}$				
19. Steady viscous flow past a cylinder: (I) slow rotation, (II) no rotation. Which is true? P: Lift force zero in (I) Q: Lift force zero in (II)						

c) P, S

b) $0.1 \text{ m}^3/\text{s}$ c) $0.01 \text{ m}^3/\text{s}$ d) $0.003 \text{ m}^3/\text{s}$

20. Orifice plate (60 mm diameter, discharge coefficient 0.6) measures air flow ($\rho = 1.2 \, \text{kg/m}^3$, $\mu = 1.8 \times 10^{-5} \, \text{kg m}^{-1} \, \text{s}^{-1}$) in a 100 mm pipe. Manometer reading 180 mm

d) Q, R

(GATE 2007 XE)

R: Drag force non-zero in (I) S: Drag force zero in (II)

b) P, R, S

(GATE 2007 XE)

of water. Air flow rate is:

a) P, Q, R

a) $0.3 \,\mathrm{m}^3/\mathrm{s}$

15. A model (length 20 cm) studies water flow ($v = 10^{-6} \text{ m}^2/\text{s}$) in a 5 m channel. The

model's kinematic viscosity should be:

- 21. Airstream velocity ($\rho = 1.0 \,\mathrm{kg/m^3}$) measured with a Pitot-static tube, manometer difference 2 cm of water. Velocity is: (GATE 2007 XE)
 - a) $0.02 \,\text{m/s}$
- b) 2.0 m/s
- c) 10 m/s
- d) 20 m/s
- 22. Match the following columns using the most appropriate combinations:

TABLE 22.: Table-1

- P. Volume flow rate
- 1. Quality

Q. Lift

- 2. Variable density atmosphere
- R. Stream function
- 3. Mach number

- S. Compressibility
- 4. Circulation
- 5. Reynolds number
- Correct matching is:

(GATE 2007 XE)

a) P-3, Q-4, R-1, S-5

c) P-4, Q-5, R-2, S-3

b) P-1, Q-2, R-4, S-3

- d) P-2, Q-4, R-1, S-3
- 23. A line source and sink of unit strength at x = -1 and x = +1. Velocity at (0,1) in Cartesian unit vectors i, j is: (GATE 2007 XE)
 - a) 0i + 0i
- b) $\frac{1}{2\pi} \mathbf{i} + 0\mathbf{j}$ c) $0\mathbf{i} + \frac{1}{2\pi} \mathbf{j}$
- d) $\frac{1}{\pi}$ **i** + 0**j**
- 24. Source and sink in a uniform stream correspond to:

(GATE 2007 XE)

a) doublet

- c) flow over Rankine half-body
- b) flow over circular cylinder
- d) flow over Rankine oval
- 25. A motorboat cruises at 10 m/s. A 180 kW pump sucks water at 1 m³/s and ejects it at 10 m/s relative to the lake. Total drag on the boat is:

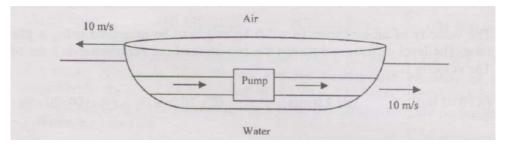


Fig. 25..1: Motor Boat

- b) 20 kN c) 10 kN a) 30 kN d) 0kN 26. From Q25, Power utilized for propelling the boat is: (GATE 2007 XE) a) 130 kW b) 100 kW c) 80 kW d) 30 kW
- 27. Fully developed laminar flow in a pipe (radius R) with axial velocity:

$$u(r) = \frac{-R^2}{4\mu} \frac{dp}{dx} \left(1 - \frac{r^2}{R^2} \right).$$

Wall shear stress magnitude τ_{wall} is:

(GATE 2007 XE)

- a) $\frac{4\mu U_m}{R}$
- b) ρuR
- c) $\frac{\mu U_m}{R}$
- d) $-\frac{R}{2}\frac{dp}{dx}$

28. Local friction factor C_f with $y = \frac{dp}{dx}$ is:

(GATE 2007 XE)

- a) $\frac{16\mu^2}{\rho^2 R^3 y}$
- b) $\frac{24\mu^2}{\rho^2 R^3 y}$ c) $\frac{64\mu^2}{\rho^2 R^3 y}$
- d) $\frac{2\mu y}{\rho R}$

-END OF SECTION-

SECTION E: MATERIAL SCIENCE

a) high elastic modulus, low melting point, high coefficient of thermal expansion b) low elastic modulus, high melting point, low coefficient of thermal expansion b) low elastic modulus, high melting point, low coefficient of thermal expansion c) low elastic modulus, low melting point, high coefficient of thermal expansion c) low elastic modulus, low melting point, high coefficient of thermal expansion c) low elastic modulus, low melting point, high coefficient of thermal expansion c) low elastic modulus, low melting point, high coefficient of thermal expansion c) low elastic modulus, low melting point, high coefficient of thermal expansion c) low elastic modulus, low melting point, high coefficient of thermal expansion c) low elastic modulus, low melting point, high coefficient of thermal expansion d) low elastic modulus, low melting point, high coefficient of thermal expansion c) low elastic modulus, low melting point, high coefficient of thermal expansion d) low elastic modulus, low melting point, high coefficient of thermal expansion d) low elastic modulus, low melting point, high coefficient of thermal expansion d) low elastic modulus, low melting point, high coefficient of thermal expansion d) low elastic modulus, low melting point, high coefficient of thermal expansion d) low elastic modulus, low melting point, high coefficient of thermal expansion d) low elastic modulus, low melting point, high coefficient of thermal expansion d) low elastic modulus, low melting point, high coefficient of thermal expansion d) low elastic modulus, low melting point, high coefficient of thermal expansion d) low elastic modulus, low melting point, high coefficient of thermal expansion d) low elastic modulus, low melting point, high coefficient of thermal expansion d) low elastic modulus, low elas	1. High bond energy in	a crystal leads to:			(GATE 2007 XE)
a) SiO ₂ b) B ₂ O ₃ c) P ₂ O ₅ d) Al ₂ O ₃ 3. Diffusion mechanism with lowest activation energy is: (GATE 2007 XE) a) Lattice diffusion c) Surface diffusion b) Grain boundary diffusion d) Diffusion through dislocations 4. In tensile test, necking starts at: (GATE 2007 XE) a) lower yield point c) ultimate tensile stress b) upper yield point d) proof stress 5. Si is added to transformer grade steel to: (GATE 2007 XE) a) decrease magnetic permeability b) decrease electrical resistivity d) increase magnetic permeability b) decrease electrical resistivity d) increase magnetic permeability 6. According to galvanic series, the most active metal among: Mg, Zn, Sn, Al is: (GATE 2007 XE) a) Mg b) Zn c) Sn d) Al 7. Enthalpy of vacancy formation in Cu is 120 kJ/mol. Equilibrium fraction of vacant lattice sites in Cu at 1000 K is: (GATE 2007 XE)	point, high coeffi pansion b) low elastic mod point, low coeffice	dulus, high melting		point, low coeffice pansion low elastic mood point, high coeffice	cient of thermal ex- lulus, low melting
3. Diffusion mechanism with lowest activation energy is: (GATE 2007 XE) a) Lattice diffusion b) Grain boundary diffusion c) Surface diffusion d) Diffusion through dislocations 4. In tensile test, necking starts at: (GATE 2007 XE) a) lower yield point b) upper yield point c) ultimate tensile stress d) proof stress 5. Si is added to transformer grade steel to: (GATE 2007 XE) a) decrease magnetic permeability b) decrease electrical resistivity d) increase magnetic permeability b) decrease electrical resistivity d) increase magnetic permeability 6. According to galvanic series, the most active metal among: Mg, Zn, Sn, Al is: (GATE 2007 XE) a) Mg b) Zn c) Sn d) Al 7. Enthalpy of vacancy formation in Cu is 120 kJ/mol. Equilibrium fraction of vacant lattice sites in Cu at 1000 K is: (GATE 2007 XE)	2. Which oxide does N	OT form glass by itse	elf?		(GATE 2007 XE)
a) Lattice diffusion b) Grain boundary diffusion c) Surface diffusion d) Diffusion through dislocations 4. In tensile test, necking starts at: (GATE 2007 XE) a) lower yield point b) upper yield point c) ultimate tensile stress d) proof stress 5. Si is added to transformer grade steel to: (GATE 2007 XE) a) decrease magnetic permeability b) decrease electrical resistivity c) improve ductility d) increase magnetic permeability b) decrease electrical resistivity d) increase magnetic permeability 6. According to galvanic series, the most active metal among: Mg, Zn, Sn, Al is: (GATE 2007 XE) a) Mg b) Zn c) Sn d) Al 7. Enthalpy of vacancy formation in Cu is 120 kJ/mol. Equilibrium fraction of vacant lattice sites in Cu at 1000 K is: (GATE 2007 XE)	a) SiO_2	b) B_2O_3	c)	P_2O_5	d) Al_2O_3
b) Grain boundary diffusion d) Diffusion through dislocations 4. In tensile test, necking starts at: (GATE 2007 XE) a) lower yield point b) upper yield point c) ultimate tensile stress d) proof stress 5. Si is added to transformer grade steel to: (GATE 2007 XE) a) decrease magnetic permeability b) decrease electrical resistivity d) increase magnetic permeability 6. According to galvanic series, the most active metal among: Mg, Zn, Sn, Al is: (GATE 2007 XE) a) Mg b) Zn c) Sn d) Al 7. Enthalpy of vacancy formation in Cu is 120 kJ/mol. Equilibrium fraction of vacant lattice sites in Cu at 1000 K is: (GATE 2007 XE)	3. Diffusion mechanism	n with lowest activation	on ei	nergy is:	(GATE 2007 XE)
a) lower yield point c) ultimate tensile stress b) upper yield point d) proof stress 5. Si is added to transformer grade steel to: (GATE 2007 XE) a) decrease magnetic permeability b) decrease electrical resistivity d) increase magnetic permeability 6. According to galvanic series, the most active metal among: Mg, Zn, Sn, Al is: (GATE 2007 XE) a) Mg b) Zn c) Sn d) Al 7. Enthalpy of vacancy formation in Cu is 120 kJ/mol. Equilibrium fraction of vacant lattice sites in Cu at 1000 K is: (GATE 2007 XE)	· · · · · · · · · · · · · · · · · · ·	diffusion			
b) upper yield point d) proof stress 5. Si is added to transformer grade steel to: (GATE 2007 XE) a) decrease magnetic permeability b) decrease electrical resistivity d) increase magnetic permeability 6. According to galvanic series, the most active metal among: Mg, Zn, Sn, Al is: (GATE 2007 XE) a) Mg b) Zn c) Sn d) Al 7. Enthalpy of vacancy formation in Cu is 120 kJ/mol. Equilibrium fraction of vacant lattice sites in Cu at 1000 K is: (GATE 2007 XE)	4. In tensile test, necking	ng starts at:			(GATE 2007 XE)
 a) decrease magnetic permeability b) decrease electrical resistivity c) improve ductility d) increase magnetic permeability 6. According to galvanic series, the most active metal among: Mg, Zn, Sn, Al is: (GATE 2007 XE) a) Mg b) Zn c) Sn d) Al 7. Enthalpy of vacancy formation in Cu is 120 kJ/mol. Equilibrium fraction of vacant lattice sites in Cu at 1000 K is: (GATE 2007 XE)					tress
 b) decrease electrical resistivity d) increase magnetic permeability 6. According to galvanic series, the most active metal among: Mg, Zn, Sn, Al is:	5. Si is added to transfe	former grade steel to:			(GATE 2007 XE)
a) Mg b) Zn c) Sn d) Al 7. Enthalpy of vacancy formation in Cu is 120 kJ/mol. Equilibrium fraction of vacant lattice sites in Cu at 1000 K is: (GATE 2007 XE)					
7. Enthalpy of vacancy formation in Cu is 120 kJ/mol. Equilibrium fraction of vacant lattice sites in Cu at 1000 K is: (GATE 2007 XE)	6. According to galvani	ic series, the most act	ive	metal among: Mg,	
lattice sites in Cu at 1000 K is: (GATE 2007 XE)	a) Mg	b) Zn	c)	Sn	d) Al
a) 1.35×10^{-8} b) 5.39×10^{-7} c) 7.76×10^{-6} d) 2.58×10^{-9}			20 k	J/mol. Equilibriun	
	a) 1.35×10^{-8}	b) 5.39×10^{-7}	c)	7.76×10^{-6}	d) 2.58×10^{-9}

8.	8. Metal melting point 1000 K, enthalpy of melting 2.0×10^9 J/m³, solid-liquid interface energy 0.5 J/m². Radius of critical nucleus during solidification at 900 K is: (GATE 2007 XE)					
	a)	10.0 nm	b) 5.0 nm	c)	5.0 μm	d) 2.5 nm
9.		binary system A-B ion are:	at 1 atm, parameters	ind	ependently varied i	n two phase $(\alpha + \beta)$ (GATE 2007 XE)
		ature	phase and temperand β phases		either composition temperature temperature only	n of α or β phase or
10.	Cď	++ doped NaCl cry	stal has higher condu	ıctiv	vity at room temp	due to:
						(GATE 2007 XE)
		movement	energy for cation vacancy concentra-		introduction of he increase in anion tion	oles in crystal vacancy concentra-
11.	Ma	tch heat treatment	s (P, Q, R, S) with m	icro	estructure (1-5) in h	nypoeutectoid steel: (GATE 2007 XE)
			TABLE 11.: 7	Гаb	le-2	
Q: R:	Ma Ful	stempering rtempering I annealing ench hardening + t	empering at 700 °C	2. 3. 4.	Martensite Ferrite + Spheroid Ferrite + coarse p Bainite Tempered martens	earlite
		P-4, Q-1, R-3, S-P-5, Q-1, R-3, S-			P-1, Q-4, R-2, S-P-2, Q-5, R-3, S-	
12.			er X-ray diffraction pagth 0.154 nm. Lattice			Bragg angle 23.21° (GATE 2007 XE)
	a)	0.391	b) 0.338	c)	0.276	d) 0.437

13.	Which direct	ion lies in (111) plane	e?		(GATE 2007 Z	XE)
	a) (211)	b) (110)		c) (100)	d) (112)	
14.	Yield strengt	h varies with grain size	ze d as	s:	(GATE 2007 Z	XE)
	a) $d^{-1/2}$	b) d^{-1}		c) <i>d</i>	d) $d^{1/2}$	
15.	Toughening posite: XE)	mechanism NOT cont	ributin	g in SiC whisker	reinforced alumina co (GATE 2	
		deflection nation toughening across crack face		d) energy abso out	orbed during whisker p	ull-
16.	Match experi	mental techniques (P,	Q, R,	S) with application	ons (1-5): (GATE 2007 X	Œ)
		TABI	LE 16.	: Table-3		
Q: R:	P: X-ray diffraction Q: Transmitted polarized light microscopy R: Four probe technique S: Zone refining			 Resistivity determination Measurement of crystallite size Observation of inclusions Observation of spherulites Purification of materials 		
	a) P-2, Q-3, b) P-4, Q-3,			c) P-4, Q-3, R d) P-2, Q-4, R		
17.	Match polym	ers (P, Q, R, S) with	applic	ations (1-5):	(GATE 2007 Z	XE)
		TABI	LE 17.	: Table-4		
		P: Polycarbonates Q: Fluorocarbons R: Polyaniline S: Polypropylene	 Pa Ot M 	nti-adhesive coatin ackaging film atdoor light globes agnetic recording olymer LEDs	S	
	a) P-2, Q-1, b) P-4, Q-1,			c) P-3, Q-1, R d) P-3, Q-1, R		

18.	3. Match materials (P, Q, R, S) with applications (1-5):							
	TABLE 18.: Table-5							
	P: GaAs _{1-x} P _x Q: MgB ₂ R: Hydroxyapatite S: Kevlar TM fibers	 Bull LEI Abra 	 Prosthetics Bulletproof jackets LEDs Abrasives Superconducting magnets 					
				(GATE 2007 XE)				
	a) P-3, Q-5, R-1, S-2 b) P-3, Q-5, R-4, S-2		c) P-5, Q-4, R-1, S d) P-3, Q-5, R-4, S					
19.	Optical transparency of a single crystal depends on:		(GATE 2007 XE)					
	a) Band gapb) Lattice parameter		c) Crystal structured) Work function					
20.	Drift mobility of electrons in intrinsic region of doped semiconductor as function temperature: (GATE 2007 X							
	a) limited by ionized impurity singb) limited by phonon scattering		c) limited by pointd) remains unaffect					
21.	$ZnFe_2O_4$ has inverse spinel structure. Atomic numbers of Zn, Fe, O are 30, 26, 8 respectively. Net magnetic moment per formula unit in Bohr magnetons (μ_B) is: (GATE 2007 XE)							
	a) 2 μ_B b) 1 μ_B		c) 4 μ_B	d) $0 \mu_B$				
22.	Nb_3 Sn is widely used in supercon	ducting	magnets because	(GATE 2007 XE)				

a) Type I superconductor

critical magnetic field

b) Type II superconductor with large

c) T_c above helium boiling point d) It is an intermetallic

	neighbor distance (nm) is:		,	(GATE 2007 XE)		
	a) 0.223	b) 0.273	c) 0.136	d) 0.1575		
24.	Theoretical density of	of Mo (kg/m ³) is:		(GATE 2007 XE)		
	a) 20400	b) 2550	c) 10200	d) 5100		
25.	A continuous carbon Elastic modulus of a epoxy 1200 kg/m ³ . I					
	a) 1440	b) 1200	c) 1800	d) 1340		
26.	Specific modulus of	elasticity of composit	e in longitudinal direc	tion is: (GATE 2007 XE)		
	a) 2.76 MPa·m³/kgb) 112.11 GPa		 c) 161.44 GPa d) 112.11 MPa·m³/k 	g		
27.			$0.45 \times 10^{16} \text{ m}^{-3}$. Sample 28. Number of As ato			
	a) 5.01×10^{22}	b) 5.01×10^{26}	c) 5.01×10^{19}	d) 3.929×10^{23}		
28.	Assuming all impuri	(GATE 2007 XE)				
	a) 2.894×10^{-7} b) 4.197×10^{0}		c) 4.197×10^5 d) 4.197×10^{12}			
—END OF SECTION—						

23. Mo has BCC with lattice parameter 0.315 nm, atomic mass 96. Mo-Mo nearest